

# 2SC2315 2SC2316

## Silicon NPN Triple Diffused Mesa

☆ Super Beta Transistor

**Application Example:**  
General Purpose

● Outline Drawing 1 ..... MT-25(TO220)

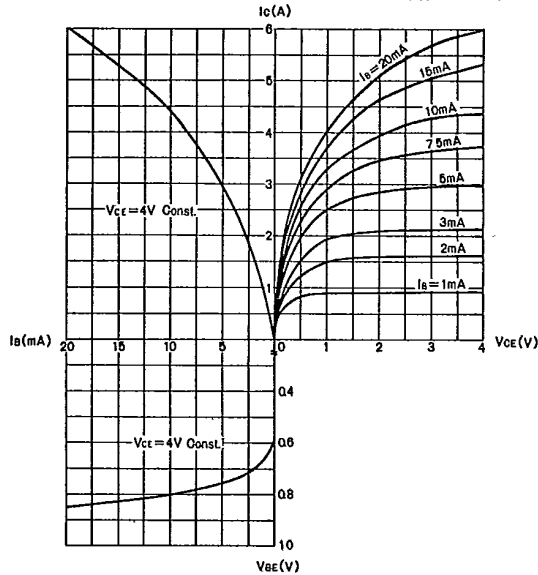
### Absolute Maximum Ratings

Symbol	2SC2315	2SC2316	Unit
$V_{CB0}$	80	100	V
$V_{CE0}$	60	80	V
$V_{EBO}$	6		V
$I_C$	6		A
$I_B$	3		A
$P_C$	50 ( $T_{FL} = 25^\circ\text{C}$ )		W
$T_J$	150		$^\circ\text{C}$
$T_{stg}$	-55 ~ +150		$^\circ\text{C}$

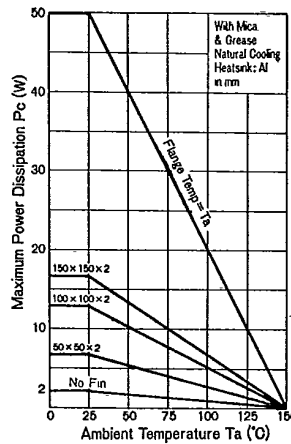
### Electrical Characteristics

Symbol	Conditions	2SC2315	2SC2316	Unit
$I_{CBO}$		100max	100max	$\mu\text{A}$
	$V_{CB} =$	80	100	V
$I_{EBO}$	$V_{EB} = 6\text{V}$	1.0max		mA
$V_{(BR)CEO}$	$I_C = 25\text{mA}$	60min	80min	V
$h_{FE}$	$V_{CE} = 4\text{V}, I_C = 0.5\text{A}$	500min		
$V_{CE(sat)}$	$I_C = 3\text{A}, I_B = 0.06\text{A}$	1.0max		V
$f_T$	$V_{CE} = 12\text{V}, I_E = -0.5\text{A}$	30typ		MHz

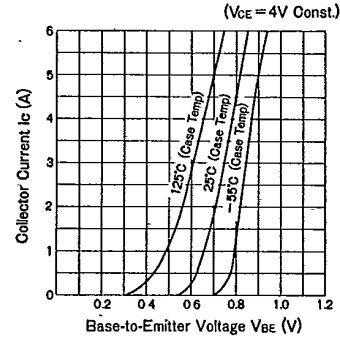
### Common Emitter Characteristics (Typical Value)



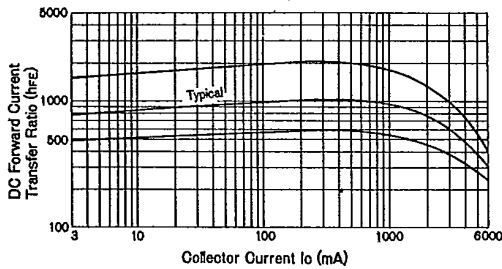
### Power Derating



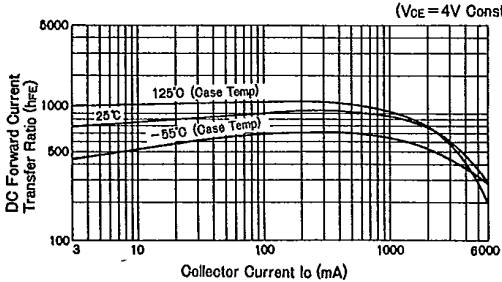
### Temperature Characteristics



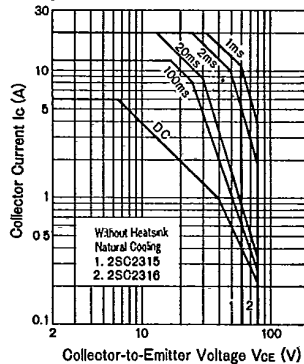
### DC Current Gain Characteristics



### DC Current Gain Temperature Characteristics



### Maximum Areas For Safe Operation (ASO) (Single Pulse)



### Collector-to-Emitter Saturation Characteristics

